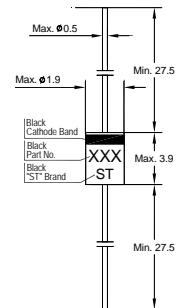


Silicon Epitaxial Planar Switching Diode
Features

- Fast switching speed
- High reliability


 Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	75 200	mA
Forward Continuous Current	I_{FM}	150 300	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	1 1 4	A
		at $t = 1$ s	
		at $t = 1$ μ s	
		at $t = 1$ μ s	
Power Dissipation	P_{tot}	500	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V_F	0.62	0.72	V
at $I_F = 5$ mA	1N914B			
at $I_F = 100$ mA	1N914B	-	1	
at $I_F = 10$ mA	1N914	-	1	
at $I_F = 20$ mA	1N914A	-	1	
Reverse Current	I_R	-	25	nA
at $V_R = 20$ V		-	5	μ A
at $V_R = 75$ V		-	50	μ A
at $V_R = 20$ V, $T_j = 150^\circ\text{C}$				
Diode Capacitance	C_j	-	4	pF
at $V_R = 0$, $f = 1$ MHz				
Reverse Recovery Time	t_{rr}	-	4	ns
at $I_F = 10$ mA to $I_R = 1$ mA, $V_R = 6$ V, $R_L = 100 \Omega$				